

ABSTRACT OF THE DISCLOSURE

The semiconductor device comprises: an interlayer insulating film 405 and an insulating film 409, interconnect
5 lines 407, 408a and 408b embedded in the insulating film 409, circuit elements 410a and 410b mounted on the insulating film 409, a packaging film 415 formed so as to cover the circuit elements 410a and 410b, and an electroconductive shielding film 416 formed so as to cover the packaging film 415. The
10 interconnect lines 408a and 408b are configured to be electrically coupled to the shielding film 416.